

Title (en)

METHOD FOR PRODUCING AN OHMIC CONTACT

Title (de)

VERFAHREN ZUM HERSTELLEN EINES OHMSCHEN KONTAKTS

Title (fr)

PROCEDE POUR REALISER UN CONTACT OHMIQUE

Publication

EP 1116263 A2 20010718 (DE)

Application

EP 99969531 A 19990910

Priority

- DE 9902875 W 19990910
- DE 19843648 A 19980923

Abstract (en)

[origin: DE19939107A1] Silicon carbide component production comprises ohmic contact formation before high temperature epitaxial layer growth. Production of a component having a silicon carbide substrate (1) with ohmic and Schottky contacts comprises applying an ohmic contact metallization on the substrate back face prior to growing an epitaxial layer on the substrate front face at above 1300 deg C and applying Schottky contact metallization on the epitaxial layer. Preferred Features: The ohmic contact metal is Nb, Ta, Mo or W.

IPC 1-7

H01L 21/285; H01L 29/45; H01L 21/329; H01L 29/872

IPC 8 full level

H01L 21/28 (2006.01); **H01L 21/04** (2006.01); **H01L 29/24** (2006.01); **H01L 29/43** (2006.01); **H01L 29/45** (2006.01); **H01L 29/47** (2006.01); **H01L 29/872** (2006.01)

CPC (source: EP US)

H01L 21/0485 (2013.01 - EP US); **H01L 29/1608** (2013.01 - EP US); **H01L 29/45** (2013.01 - EP US); **H01L 29/47** (2013.01 - EP US); **H01L 29/6606** (2013.01 - EP US); **H01L 29/872** (2013.01 - EP US); **Y10S 438/931** (2013.01 - EP US)

Citation (search report)

See references of WO 0017919A2

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